

isc N-Channel MOSFET Transistor

IRFP451

FEATURES

- Drain Current -I_D= 13A@ T_C=25°C
- · Drain Source Voltage-
- : V_{DSS}= 450V(Min)
- · Static Drain-Source On-Resistance
 - : $R_{DS(on)} = 0.4 \Omega (Max)$
- Fast Switching
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



DESCRIPTION

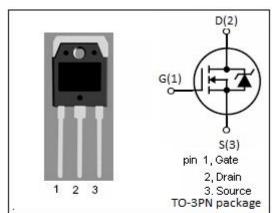
• Designed for use in switch mode power supplies and general purpose applications.

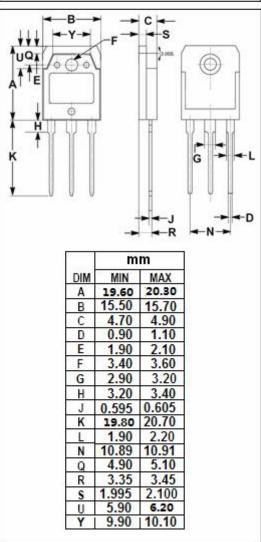
ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage		V
V _{GS}	Gate-Source Voltage-Continuous	±20	V
I _D	Drain Current-Continuous	13	Α
I _{DM}	Drain Current-Single Pluse	52	А
P _D	Total Dissipation @T _C =25℃ 1		W
TJ	Max. Operating Junction Temperature -55~150		$^{\circ}$
T _{stg}	Storage Temperature	-55~150	$^{\circ}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	0.7	°C/W
R _{th j-a}	Thermal Resistance, Junction to Ambient 30		°C/W







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	450		V
V _{GS(th)}	Gate Threshold Voltage	V_{DS} = V_{GS} ; I_D = 0.25mA	2	4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 7A		0.4	Ω
Igss	Gate-Body Leakage Current	V _{GS} = ±20V;V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 450V; V _{GS} = 0		250	μА
V _{SD}	Forward On-Voltage	I _S = 13A; V _{GS} = 0		1.4	V



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